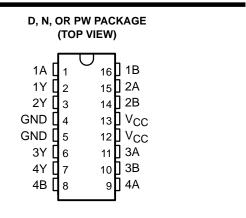
- Flow-Through Architecture Optimizes
  PCB Layout
- Center-Pin V<sub>CC</sub> and GND Configurations Minimize High-Speed Switching Noise
- EPIC<sup>™</sup> (Enhanced-Performance Implanted CMOS) 1-µm Process
- 500-mA Typical Latch-Up Immunity at 125°C
- Package Options Include Plastic Small-Outline (D) and Thin Shrink Small-Outline (PW) Packages, and Standard Plastic 300-mil DIPs (N)



### description

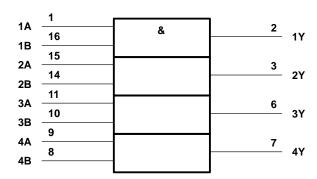
This device contains four independent 2-input AND gates. It performs the Boolean function  $Y = A \bullet B$  or  $Y = \overline{\overline{A} + \overline{B}}$  in positive logic.

The 74AC11008 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE (each gate)

INP	UTS	OUTPUT
Α	В	Y
Н	Н	Н
L	X	L
Х	L	L

### logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

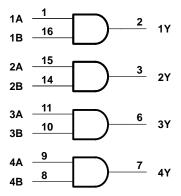


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EPIC is a trademark of Texas Instruments Incorporated.



### logic diagram (positive logic)



### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Cumply voltage reage V	051/4071/
Supply voltage range, V <sub>CC</sub>	
Input voltage range, V <sub>I</sub> (see Note 1)	0.5 V to V <sub>CC</sub> + 0.5 V
Output voltage range, V <sub>O</sub> (see Note 1)	$-0.5 \text{ V}$ to $V_{CC} + 0.5 \text{ V}$
Input clamp current, $I_{IK}$ ( $V_I < 0$ or $V_I > V_{CC}$ )	±20 mA
Output clamp current, I <sub>OK</sub> (V <sub>O</sub> < 0 or V <sub>O</sub> > V <sub>CC</sub> )	±50 mA
Continuous output current, $I_O$ ( $V_O = 0$ to $V_{CC}$ )	±50 mA
Continuous current through V <sub>CC</sub> or GND	±100 mA
Maximum power dissipation at T <sub>A</sub> = 55°C (in still air) (see Note 2)	): D package 1.3 W
	N package1.1 W
	PW package 0.5 W
Storage temperature range, Tstg	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.



NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

<sup>2.</sup> The maximum package power dissipation is calculated using a junction temperature of 150°C and a board trace length of 750 mils, except for the N package, which has a trace length of zero.

### recommended operating conditions

			MIN	NOM	MAX	UNIT
Vcc	Supply voltage		3	5	5.5	V
	V <sub>CC</sub> =		2.1			
٧ <sub>IH</sub>	High-level input voltage	$V_{CC} = 4.5 V$	3.15	-		V
		$V_{CC} = 5.5 V$	3.85			
		VCC = 3 V	2.1 3.15		0.9	
VIL	Low-level input voltage	$V_{CC} = 4.5 V$			1.35	V
		V <sub>CC</sub> = 5.5 V			1.65	
٧ı	Input voltage		0		VCC	V
٧o	Output voltage		0		VCC	V
		VCC = 3 V			-4	
ЮН	High-level output current	V <sub>CC</sub> = 4.5 V			-24	mA
		V <sub>CC</sub> = 5.5 V			-24	
		V <sub>CC</sub> = 3 V			12	
lOL	Low-level output current	V <sub>CC</sub> = 4.5 V			24	mA
	V <sub>CC</sub> = 5.5 V				24	
Δt/Δν	Input transition rise or fall rate		0		10	ns/V
TA	Operating free-air temperature		-40		85	°C

# electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

DADAMETED	TEST CONDITIONS	V	T,	<sub>A</sub> = 25°C	;	MIN MA	MAV	LIAUT
PARAMETER	TEST CONDITIONS	VCC	MIN	TYP	MAX	IVIIIVI	0.1 0.1 0.1 0.44 0.44 1.65 ±1	UNIT
		3 V	2.9			2.9		
	$I_{OH} = -50 \mu\text{A}$	4.5 V	4.4			4.4		
		5.5 V	5.4			5.4		
Vон	$I_{OH} = -4 \text{ mA}$	3 V	2.58			2.48		V
		4.5 V	3.94			3.8		
	I <sub>OH</sub> = -24 mA	5.5 V	4.94			4.8		
	$I_{OH} = -75 \text{ mA}^{\dagger}$	5.5 V				3.85	0.1 0.1 0.44 0.44 0.44 1.65 ±1	
		3 V			0.1		0.1	
	I <sub>OL</sub> = 50 μA	4.5 V			0.1		0.1	
		5.5 V			0.1		0.1	V
$V_{OL}$	I <sub>OL</sub> = 12 mA	3 V			0.36		0.1 0.1 0.44 0.44 1.65 ±1	
	la. 24 mA	4.5 V			0.36		0.44	
	I <sub>OL</sub> = 24 mA	5.5 V			0.36		0.44	
	$I_{OL} = 75 \text{ mA}^{\dagger}$	5.5 V					1.65	
lį	$V_I = V_{CC}$ or GND	5.5 V			±0.1		±1	μΑ
ICC	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			4		40	μΑ
C <sub>i</sub>	V <sub>I</sub> = V <sub>CC</sub> or GND	5 V		3.5				pF

<sup>†</sup> Not more than one output should be tested at a time, and the duration of the test should not exceed 10 ms.



## switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 3.3 V $\pm$ 0.3 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	ТО	T,	գ = 25°C	;	MIN	MAX	UNIT
FARAWETER	(INPUT)	(OUTPUT)	MIN	TYP	MAX	IVIIIV	IVIAA	ONIT
t <sub>PLH</sub>	A or B	V	1.5	6.3	9	1.5	10.2	20
tPHL	AUID	ī	1.5	5.6	7.8	1.5	8.6	ns

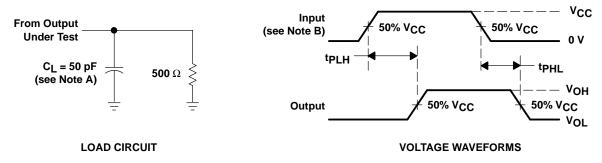
## switching characteristics over recommended operating free-air temperature range, $V_{CC}$ = 5 V $\pm$ 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM	то	T,	4 = 25°C	;	MIN	MAX	UNIT
PARAMETER	(INPUT)	(OUTPUT)	MIN	TYP	MAX	IVIIIV	N IVIAX	UNIT
<sup>t</sup> PLH	A or B	V	1.5	4.3	6.2	1.5	6.9	20
<sup>t</sup> PHL	AUID	Y	1.5	5.6	5.9	1.5	6.5	ns

### operating characteristics, $V_{CC} = 5 \text{ V}$ , $T_A = 25^{\circ}\text{C}$

	PARAMETER	TEST CONDITIONS		TYP	UNIT
C <sub>pd</sub>	Power dissipation capacitance per gate	$C_L = 50 pF$ ,	f = 1 MHz	29	pF

#### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

- B. Input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz,  $Z_O = 50 \ \Omega$ ,  $t_f = 3 \ ns$ ,  $t_f = 3 \ ns$ .
- C. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms

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